Sheet Number:	Content:
1	Info page
2	Top hierarchy.
3	144 SO DIMM male connector.
4	BOOT FLASH.
5	BUFFERS + TRANSCEIVERS.
6	FLASH MEMORY & J1 for flash write protect configuration.
7	R.T.C -Real Time Clock.
8	SRAM MEMORY.
9	SERIAL: ST16C2552 , voltage converter (ADM3202) ,serial connector.
10	TEST POINTS .
Rev Number 0.9	Preliminary release. Please make sure you have latest revision when referencing this schematic.
Rev Number 0.91	The strata flash memory address bus should be connected differently in x8 and x16 modes, in rev 0.9 it was connected for x8 mode, it should been connected in x16 mode.
Rev Number 0.92	1) The board name changed from EV-SO DIMM144 to EV-DEVICES- D144. 2) Fix the table in page 8.
Rev Number 0.93	1) New setup configuration for the SRAM - Add three pad resistors to: adsp*, adsc* and adv* signals.

Rev Number 1.0	1) Production release.
	2) The GT's write device parameters refer to Wr_n[3..0].Therefore, the write signals on the devices are connected to Wr_n [3..0]. We connected the Write_n signal, in the device module, which is DevRW_n. (This is better defined as an output enable signal). To correct it, we created a different equation in the PAL.The new equation for the Write_n signal is as follows:
	IF(!SRAM_CS_n) THEN
	Write_n=LDevRW_n # CSTiming_n;
	ELSE
	Write_n=GP_IN[0] (Wr_n0);
	END IF;
	GP_IN[0] is abbreviated on the board as follows: Wr_n0 (BE_n0 on the EV-DEVICES-D144).
	3) Fix name of U6,U4 to 74LVT162245 and U9,U10 to 28F640J3A.

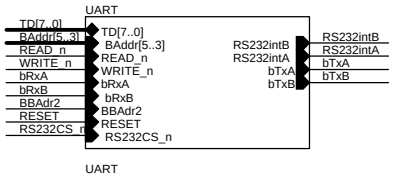
BLOCK DIAGRAM

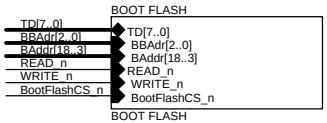
GALILEO TECHNOLOGY

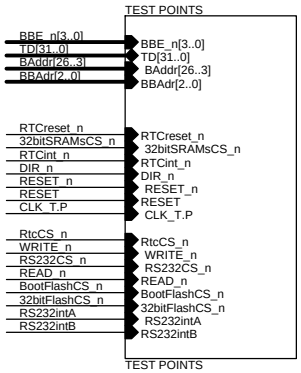
Title: EV-DEVICES-D144

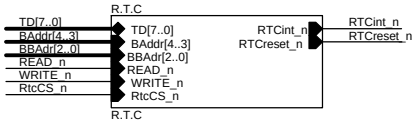
Size: B | Document Number: Info | Rev: 1.0

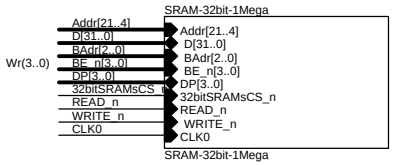
Date: Thursday, November 02, 2000 | Sheet 1 of 10

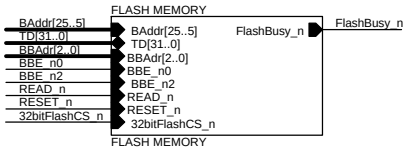


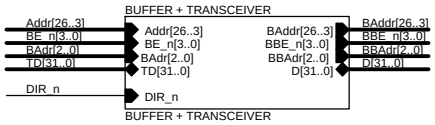


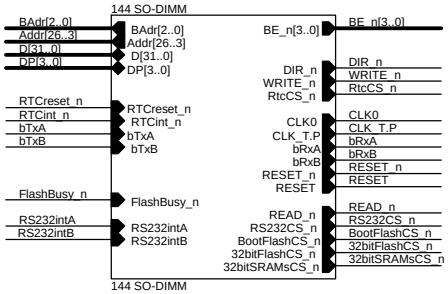




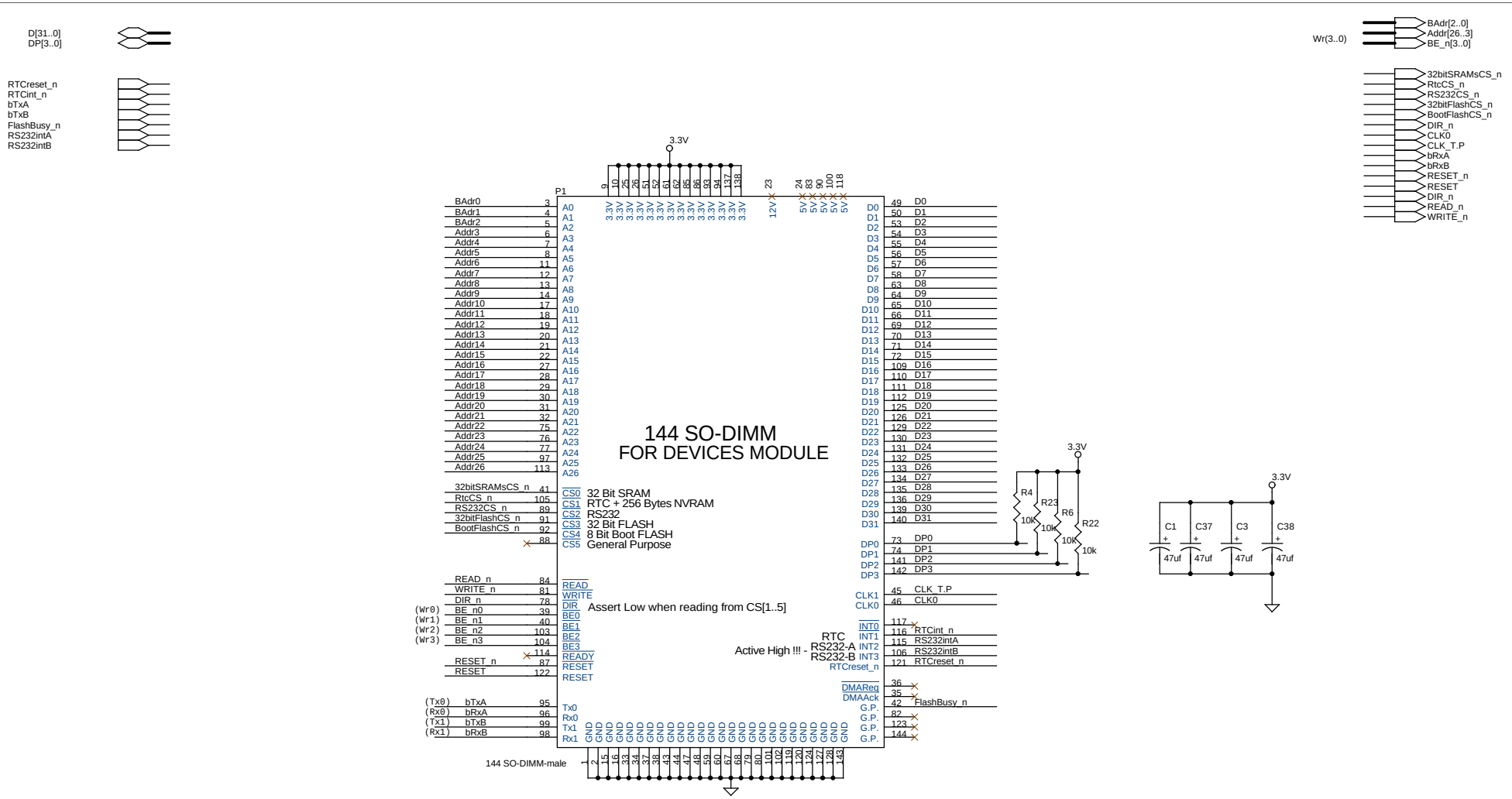








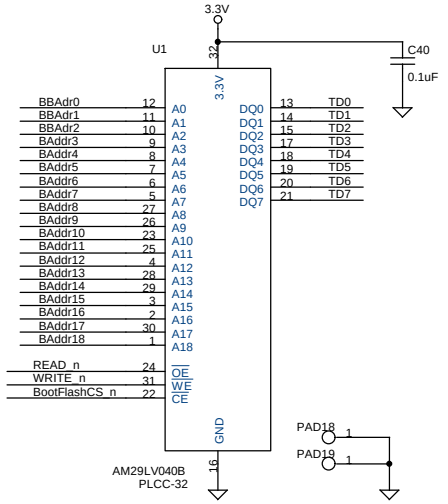
	GALILEO TECHNOLOGY	
Title	EV-DEVICES-D144	
Size B	Document Number Main	Rev 1.0
Date: Thursday, November 02, 2000	Sheet 2 of 10	



GALILEO TECHNOLOGY			
Title: EV-DEVICES-D144			
Size: B	Document Number: 144 SO-DIMM		Rev: 1.0
Date: Thursday, November 02, 2000	Sheet 3 of 10		

TD[7..0]

BBAdr[2..0]
BAddr[18..3]
BootFlashCS_n
READ_n
WRITE_n



ST`s M29W040 can also be used

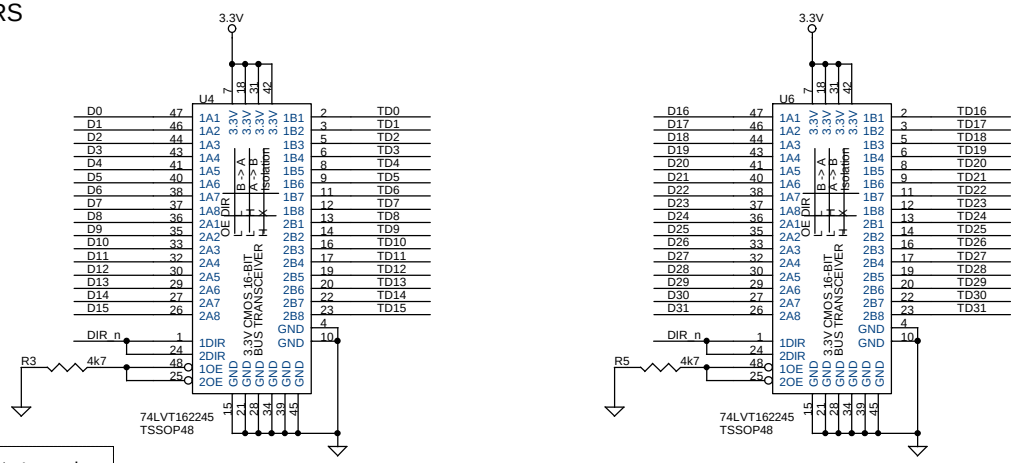
GALILEO TECHNOLOGY		
Title: EV-DEVICES-D144		
Size: B	Document Number: BOOT FLASH	Rev: 1.0
Date: Thursday, November 02, 2000	Sheet 4 of 10	

TD[31..0]
D[31..0]

Addr[26..3]
BE_n[3..0]
BAdr[2..0]
DIR_n

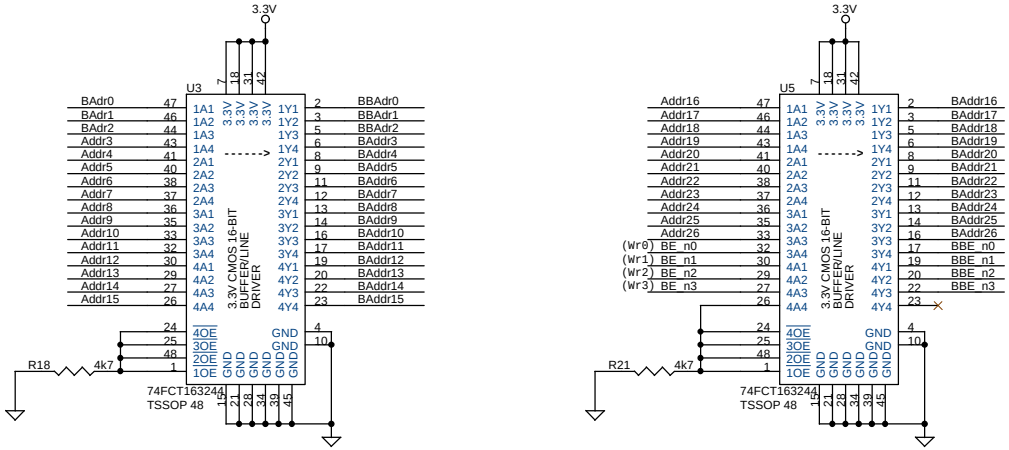
BBE_n[3..0]
BBAdr[2..0]
BAddr[26..3]

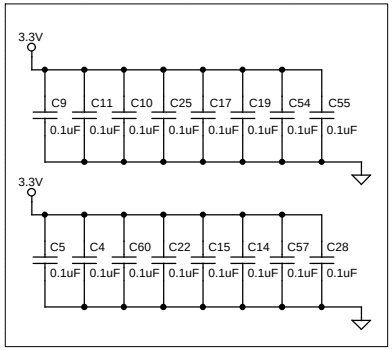
TRANSCEIVERS



DIR_n : Assert Low when reading from CS[1..5]

BUFFERS





GALILEO TECHNOLOGY		
Title: EV-DEVICES-D144		
Size: B	Document Number: BUFFER + TRANSCEIVER	Rev: 1.0
Date: Thursday, November 02, 2000	Sheet 5 of 10	

TD[31..0]

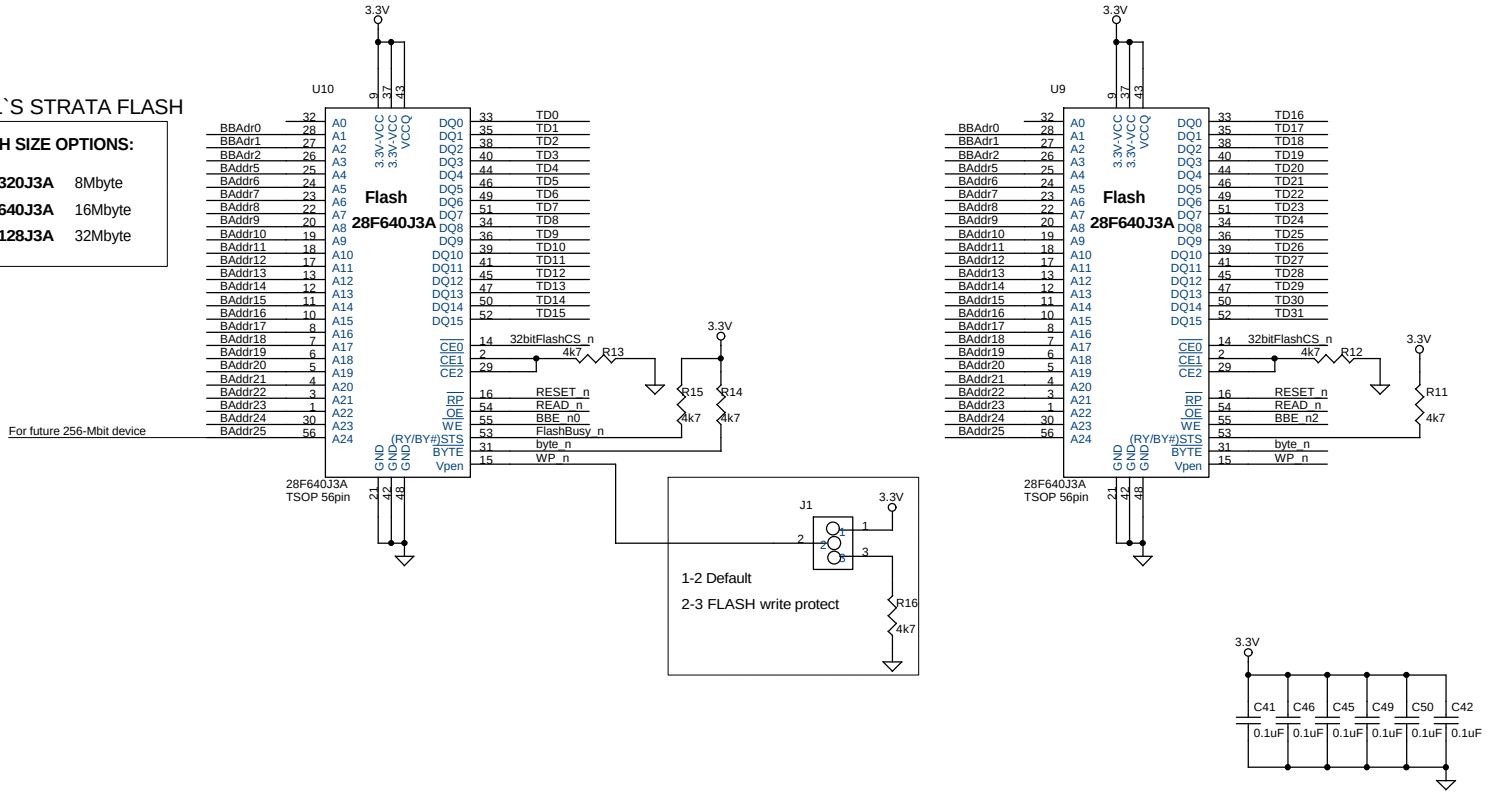
BAddr[25..5]
BBAdr[2..0]
32bitFlashCS_n
READ_n
RESET_n
BBE_n0
BBE_n2

FlashBusy_n

INTEL`S STRATA FLASH

FLASH SIZE OPTIONS:

28F320J3A	8Mbyte
28F640J3A	16Mbyte
28F128J3A	32Mbyte

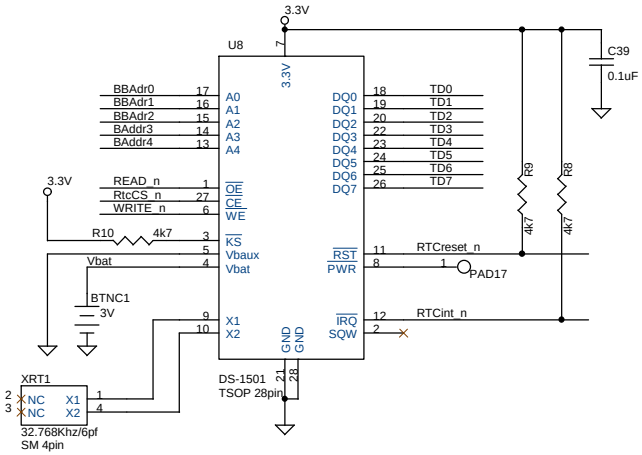


GALILEO TECHNOLOGY		
Title: EV-DEVICES-D144		
Size: B	Document Number: FLASH MEMORY	Rev: 1.0
Date: Thursday, November 02, 2000	Sheet 6 of 10	

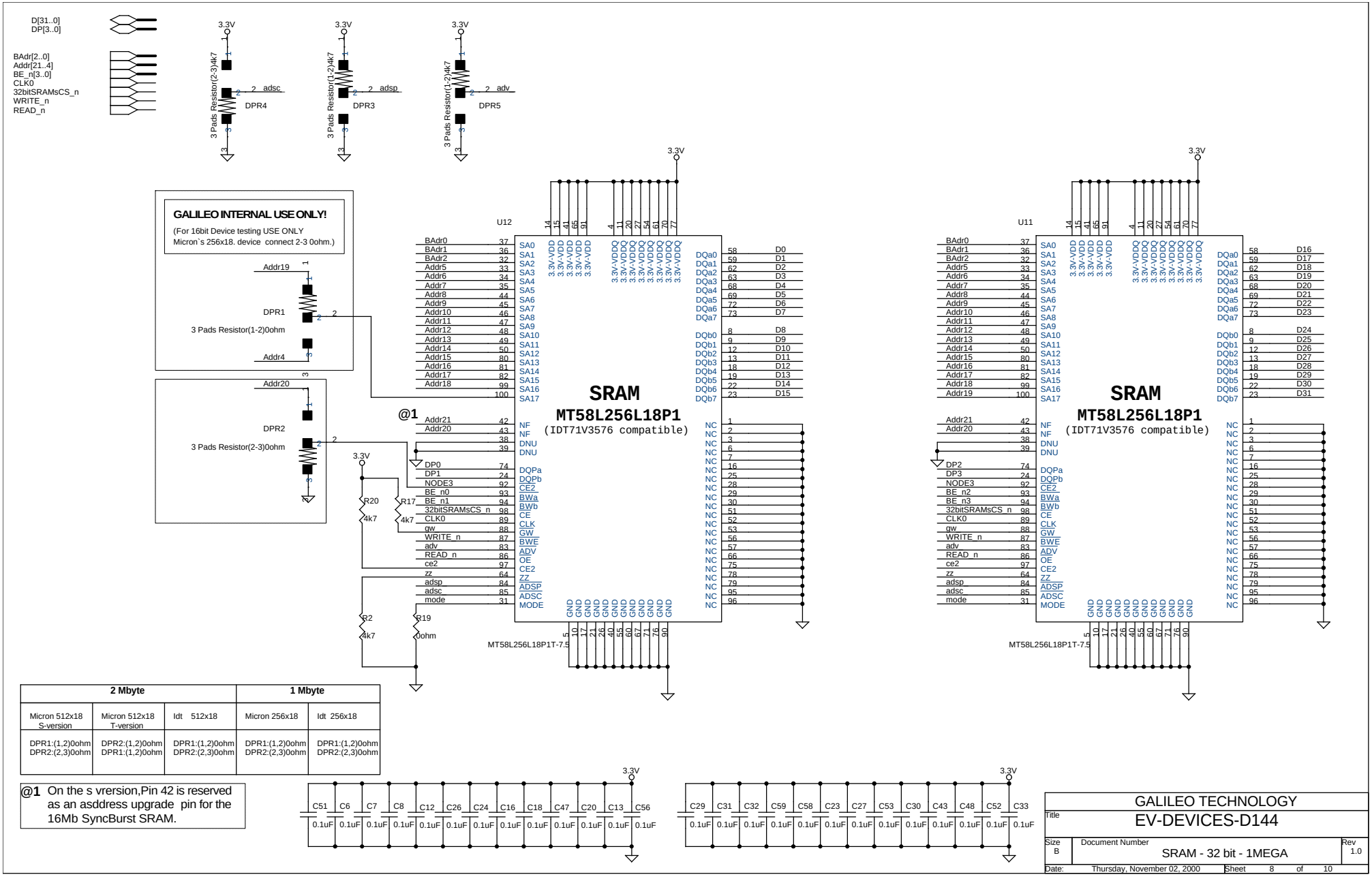
TD[7..0]

BAddr[4..3]
BBAdr[2..0]
RtcCS_n
READ_n
WRITE_n

RTCint_n
RTCreset_n



GALILEO TECHNOLOGY		
Title: EV-DEVICES-D144		
Size: B	Document Number: R.T.C	Rev: 1.0
Date: Thursday, November 02, 2000	Sheet 7 of 10	



2 Mbyte			1 Mbyte	
Micron 512x18 S-version	Micron 512x18 T-version	Idt 512x18	Micron 256x18	Idt 256x18
DPR1:(1,2)0ohm DPR2:(2,3)0ohm	DPR2:(1,2)0ohm DPR1:(1,2)0ohm	DPR1:(1,2)0ohm DPR2:(2,3)0ohm	DPR1:(1,2)0ohm DPR2:(2,3)0ohm	DPR1:(1,2)0ohm DPR2:(2,3)0ohm

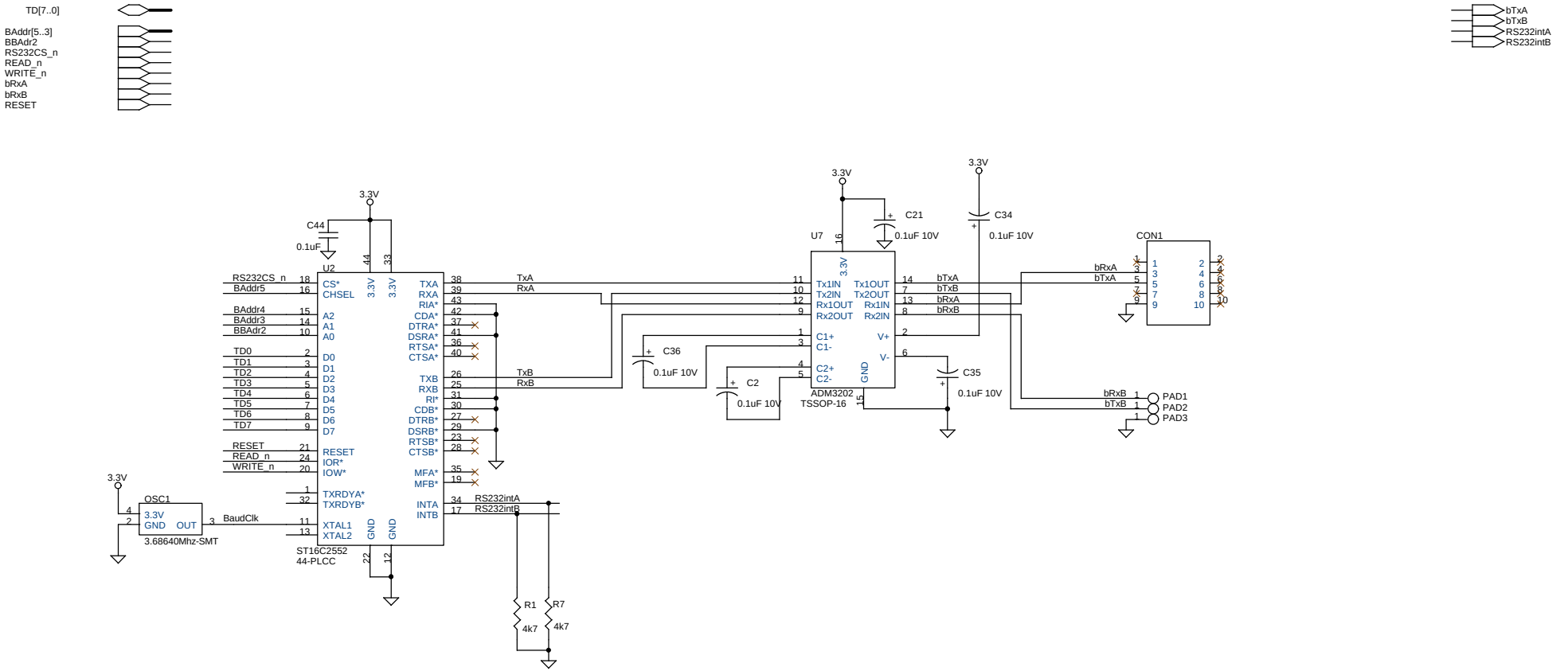
@1 On the s vrersion,Pin 42 is reserved as an asddress upgrade pin for the 16Mb SyncBurst SRAM.

GALILEO TECHNOLOGY

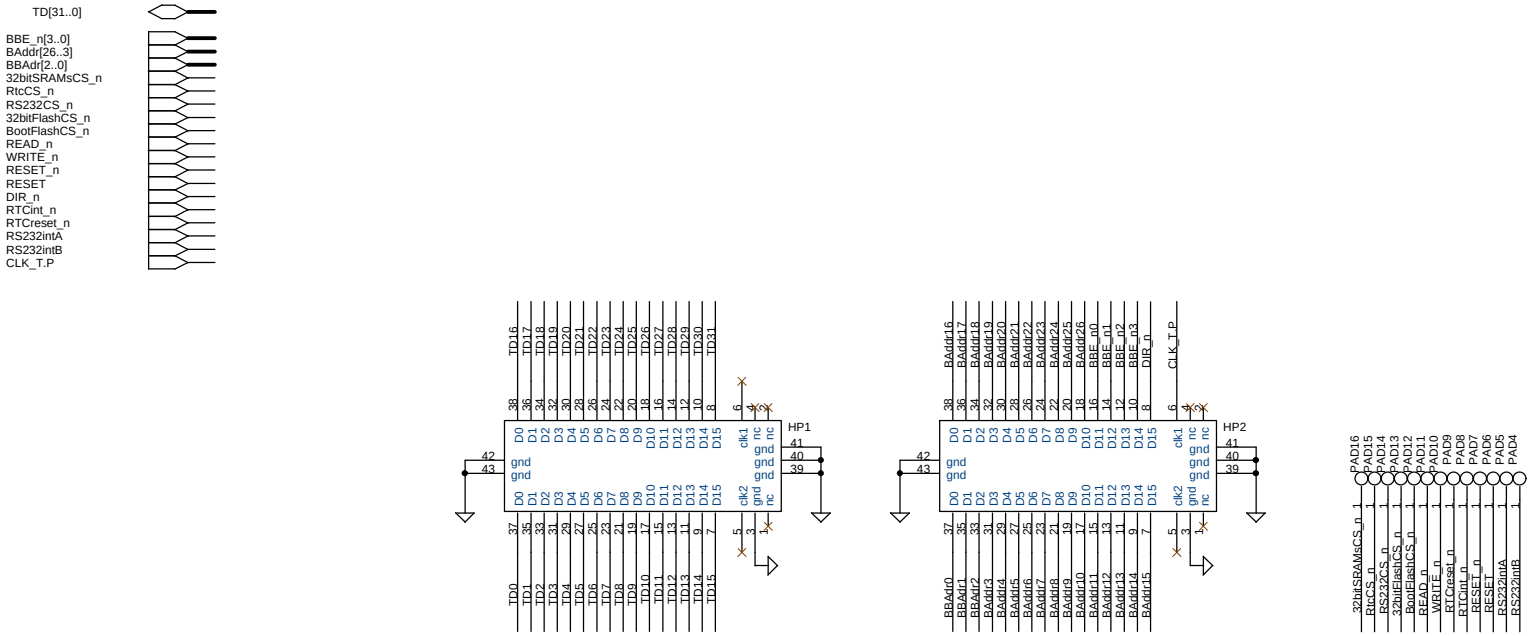
Title: EV-DEVICES-D144

Size: B | Document Number: SRAM - 32 bit - 1MEGA | Rev: 1.0

Date: Thursday, November 02, 2000 | Sheet 8 of 10



GALILEO TECHNOLOGY		
Title: EV-DEVICES-D144		
Size: B	Document Number: UART	Rev: 1.0
Date: Thursday, November 02, 2000	Sheet 9 of 10	



GALILEO TECHNOLOGY		
Title: EV-DEVICES-D144		
Size: B	Document Number: TEST POINT	Rev: 1.0
Date: Thursday, November 02, 2000	Sheet 10 of 10	